NPN SILICON RF POWER TRANSISTOR

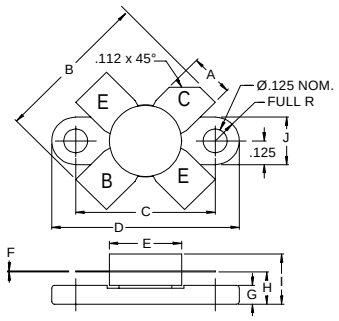
DESCRIPTION:

The **ASI BLW76** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

FEATURES:

- P_G = 18 dB min. at 75 W/30 MHz
- IMD_3 = -30 dBc max. at 75 W (PEP)
- ***Omnigold***™ Metalization System

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.05 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA			35			V
BV_{CER}	I_C = 50 mA	R_{BE} = 10 Ω		60			V
BV_{EBO}	I_E = 10 mA			4.0			V
I_{CES}	V_E = 28 V					5.0	mA
h_{FE}	V_{CE} = 5.0 V	I_C = 1.0 A		10		100	---
C_{ob}	V_{CB} = 28 V		f = 1.0 MHz			80	pF
G_{PE}	V_{CE} = 25 V	I_{CQ} = 3.2 A	f = 225 MHz	13.5	14.5		dB
IMD_3	P_{REF} = 16 W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB			-55	dBc